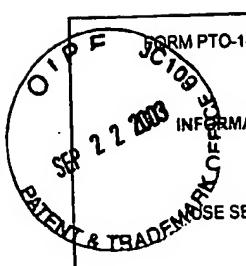


 INFORMATION DISCLOSURE STATEMENT BY APPLICANT <small>(USE SEVERAL SHEETS IF NECESSARY)</small>	ATTY. DOCKET NO. ASMEX:284DV1	APPLICATION NO. 10/626,217
	APPLICANT Pomareda, et al.	
	FILING DATE July 24, 2003	GROUP Unknown

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
CK	1 2,394,930	2/12/46	McRae			
CK	2 3,895,127	7/15/75	Comizzoli			
CK	3 4,056,642	11/1/77	Saxena et al.			
CK	4 4,292,343	9/29/81	Plaettner et al.			
CK	5 4,343,830	8/10/82	Sarma et al.			
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FOREIGN PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
						YES NO
CK	21 JP 60 254621 A	16.12.85	Patent Abstracts of Japan			
CK	22 JP 2000 160342 A	13.10.00	Patent Abstracts of Japan			
CK	23 0 617 461 A2	03/16/94	EPO			

EXAMINER <i>Christy Naracek</i>	DATE CONSIDERED <i>6/26/04</i>
<small>*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.</small>	



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ATTY. DOCKET NO.
ASMX.284DV1

APPLICATION NO.
10/626,217

APPLICANT
Pomareda, et al.

FILING DATE
July 24, 2003

GROUP
Unknown

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
CM	24	Kim, H. and R. Reif, <i>Thin Solid Films</i> , Vol. 289:192-198 (1996), "In-situ low-temperature (600°C) wafer surface cleaning by electron cyclotron resonance hydrogen plasma"
CM	25	Ramm J. and E. Beck, <i>Thin Solid Films</i> , Vol. 246:158-163 (1994), "Low temperature epitaxial growth by molecular beam epitaxy on hydrogen-plasma-cleaned silicon wafers."

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EXAMINER	Christa Karsseba	DATE CONSIDERED	6/26/04
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.			